

Fig. 1 (PRIOR ART)

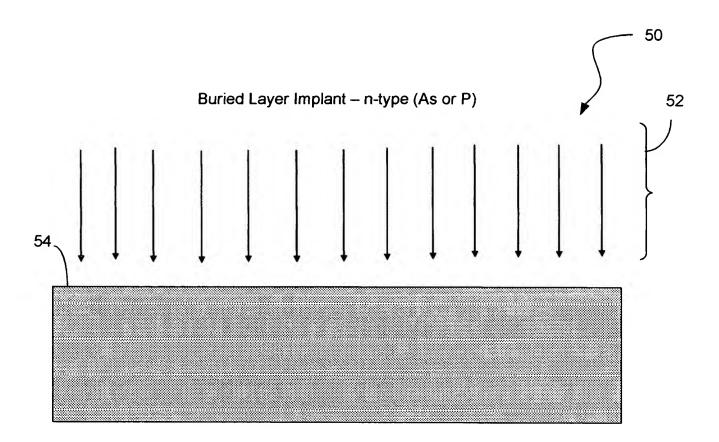


Fig. 2

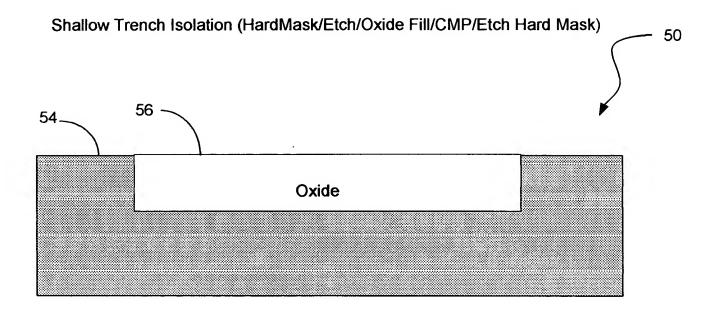


Fig. 3

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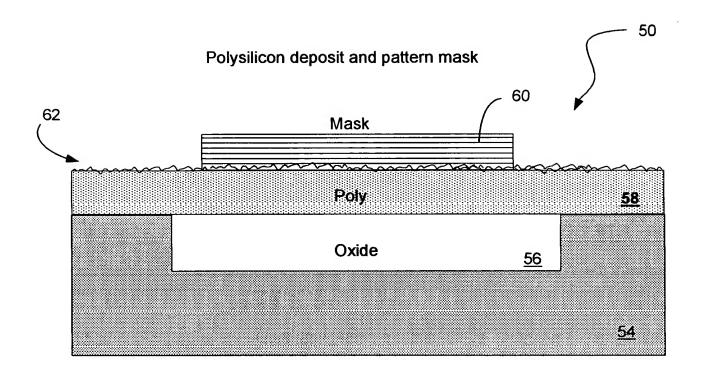
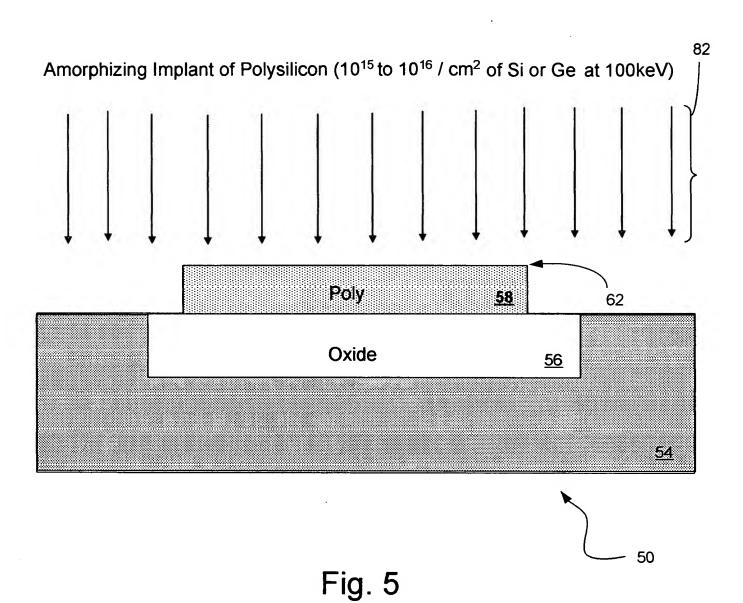


Fig. 4

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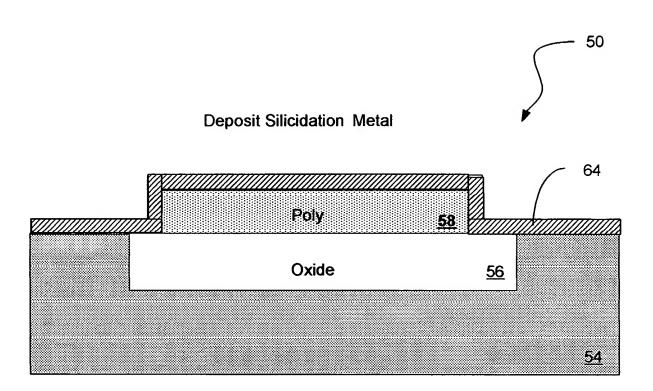


Fig. 6a

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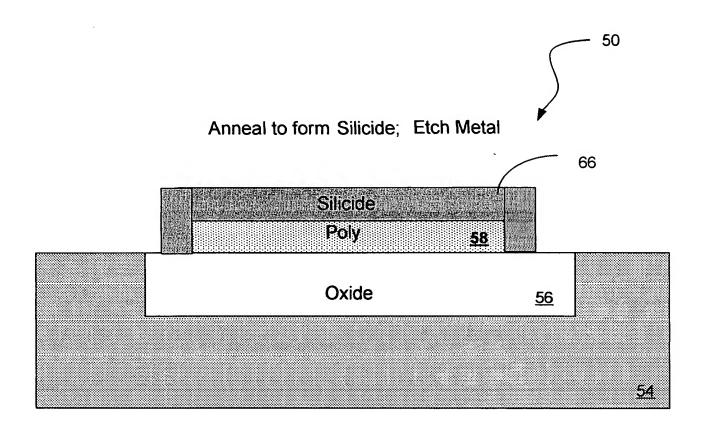


Fig. 6b

Deposit Dielectric Layer (Oxide or Nitride 500 to 5000 Angstroms)

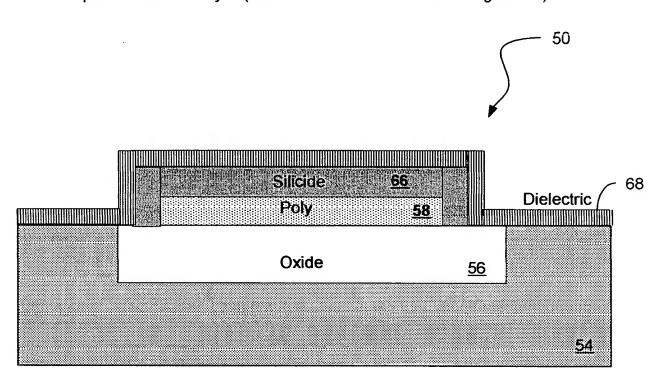


Fig. 7

Deposit Top Metal Plate (Aluminum/Copper with TiN Barrier Layer); Mask and Etch Capacitor Metal 50 Mask 72 70 Sificide Poly 58 Oxide 56

Fig. 8

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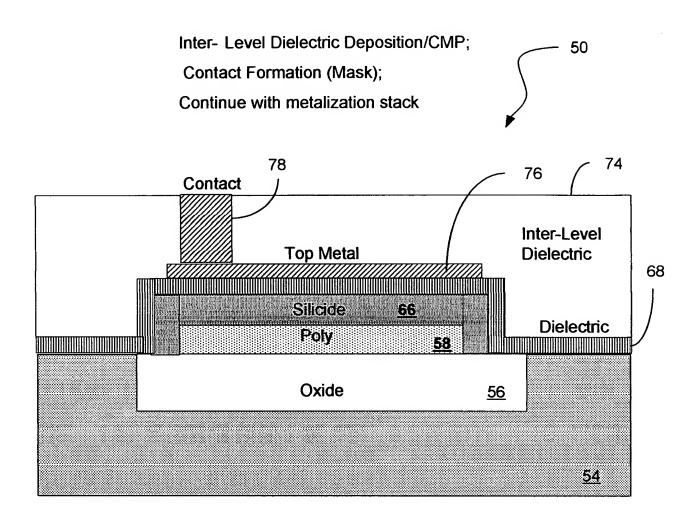


Fig. 9

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